## NSN 5962-01-203-8631

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View Online at https://aerobasegroup.com/nsn/5962-01-203-8631

0.840 inches	
Body Width:	
Between 0.220 inches and 0.310	inches
Body Height:	
0.185 inches	
Maximum Power Dissipation Ra	ating:
794.0 milliwatts	
Operating Tempurature Range:	
-55.0/+125.0 degrees celsius	
Storage Tempurature Range:	
-65.0/+150.0 degrees celsius	
Features Provided:	
3-state output and bipolar and pro	ogrammed and schottky and w/active pull-up
Inclosure Material:	
Ceramic or glass or metal	
Inclosure Configuration:	
Dual-in-line	
Output Logic Form:	
Transistor-transistor logic	
Input Circuit Pattern:	
10 input	
Case Outline Source And Desig	inator:
D-2 mil-m-38510	
Terminal Surface Treatment:	
Solder	
Voltage Rating And Type Per C	haracteristic:
-0.5 volts power source and 7.0 v	volts power source
Time Rating Per Chacteristic:	
85.00 nanoseconds propagation	delay time, low to high level output and 85.00 nanoseconds propagation delay time, high to low level
output	
Memory Device Type:	
Prom	
Test Data Document:	
96906-mil-std-883 standard (inclu	des industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:	
16 printed circuit	
Shelf Life:	
N/a	
Unit Of Measure:	

Yes - demil/mli

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**Fiig:** A458a0

